



STT3PF30L

P-CHANNEL 30V - 0.14 Ω - 3A SOT23-6L
STripFET™ II POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STT3PF30L	30 V	<0.165 Ω	3 A

- TYPICAL R_{DS(on)} = 0.14 Ω
- STANDARD OUTLINE FOR EASY AUTOMATED SURFACE MOUNT ASSEMBLY
- LOW THRESHOLD DRIVE

DESCRIPTION

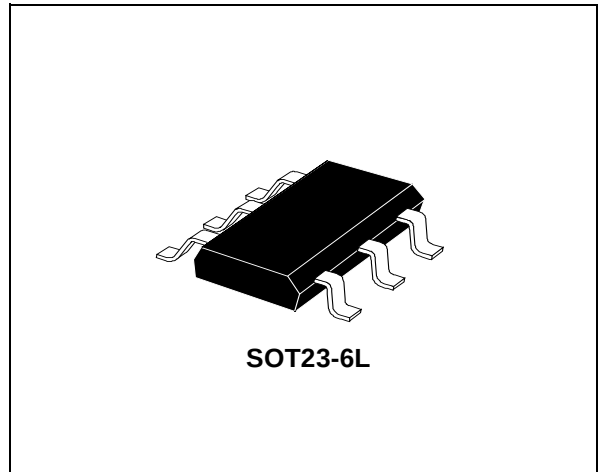
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

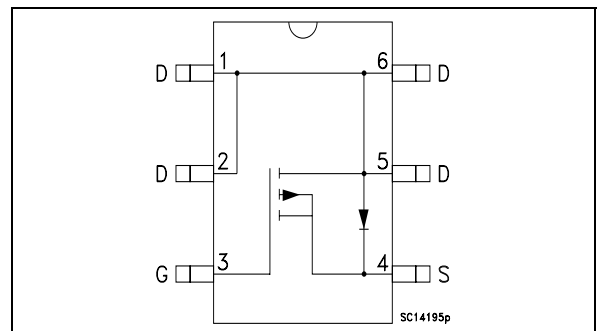
- DC MOTOR DRIVE
- DC-DC CONVERTERS
- BATTERY MANAGEMENT IN NOMADIC EQUIPMENT
- POWER MANAGEMENT IN PORTABLE/DESKTOP PCs
- CELLULAR

MARKING

- STA3



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	30	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 k Ω)	30	V
V _{GS}	Gate- source Voltage	± 16	V
I _D	Drain Current (continuous) at T _C = 25°C	2.4	A
I _D	Drain Current (continuous) at T _C = 100°C	1.5	A
I _{DM} (●)	Drain Current (pulsed)	10	A
P _{tot}	Total Dissipation at T _C = 25°C	1.6	W

(●) Pulse width limited by safe operating area.

Note: P-CHANNEL MOSFET actual polarity of voltages and current has to be reversed

STT3PF30L

THERMAL DATA

Rthj-amb	(*)Thermal Resistance Junction-ambient	Max	78	°C/W
Rthj-amb	(**)Thermal Resistance Junction-ambient	Max	156	°C/W
T _j	Max. Operating Junction Temperature		-55 to 150	°C
T _{stg}	Storage Temperature		-55 to 150	°C

(*) Mounted on a 1 inch pad of 2 oz. Cu in FR-4 board

(**) Mounted on a minimum pad of 2 oz. Cu in FR-4 board

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA, V _{GS} = 0	30			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _C = 125°C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 16 V			±100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 µA	1	1.6	2.5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 1.5 A V _{GS} = 4.5 V I _D = 1.5 A		0.14 0.16	0.165 0.2	Ω Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} =25 V I _D = 1.5 A		4		S
C _{iss} C _{oss} C _{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{DS} = 25V f = 1 MHz, V _{GS} = 0		420 95 30		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 15\text{ V}$ $I_D = 1.5\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$ (Resistive Load, Figure 1)		14.5 37		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 24\text{ V}$ $I_D = 3\text{ A}$ $V_{GS} = 4.5\text{ V}$ (see test circuit, Figure 2)		4.8 1.7 2	7	nC nC nC

SWITCHING OFF

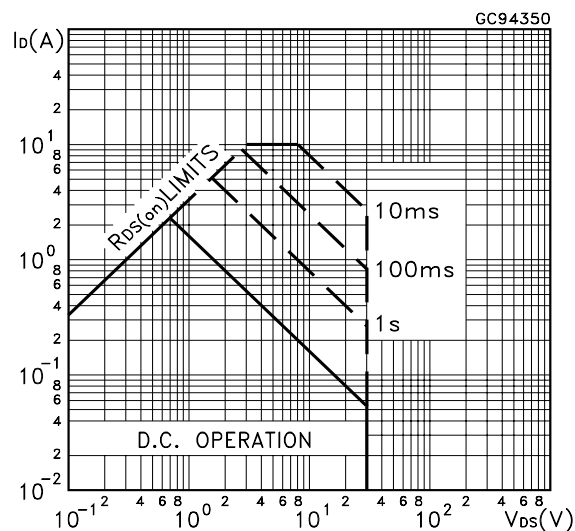
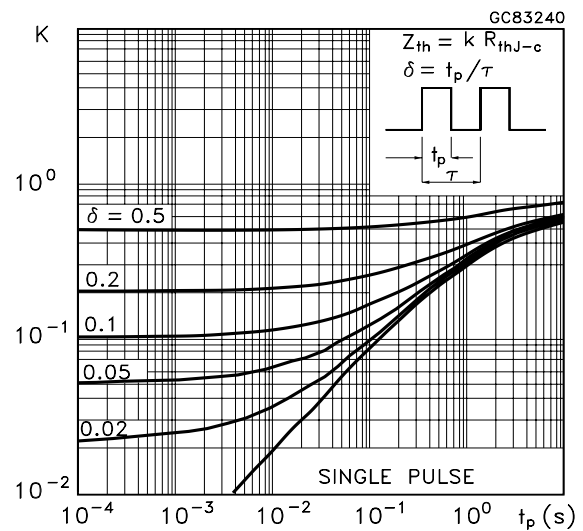
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 15\text{ V}$ $I_D = 1.5\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 4.5\text{ V}$ (Resistive Load, Figure 1)		90 23		ns ns

SOURCE DRAIN DIODE

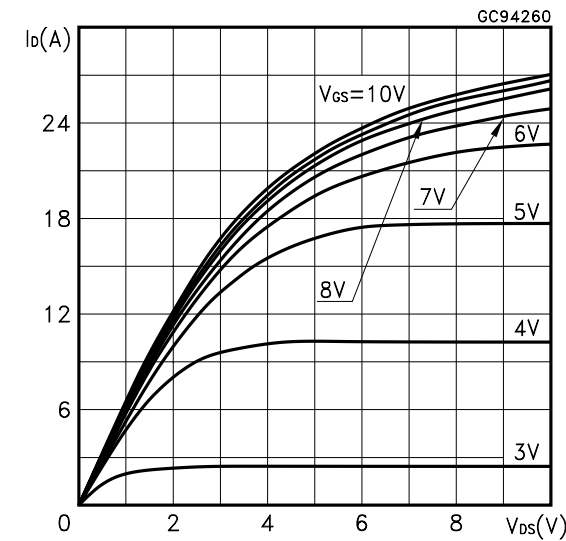
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (\bullet)$	Source-drain Current Source-drain Current (pulsed)				3 12	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 3\text{ A}$ $V_{GS} = 0$			1.2	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 3\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 15\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 3)		35 25 1.5		ns nC A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

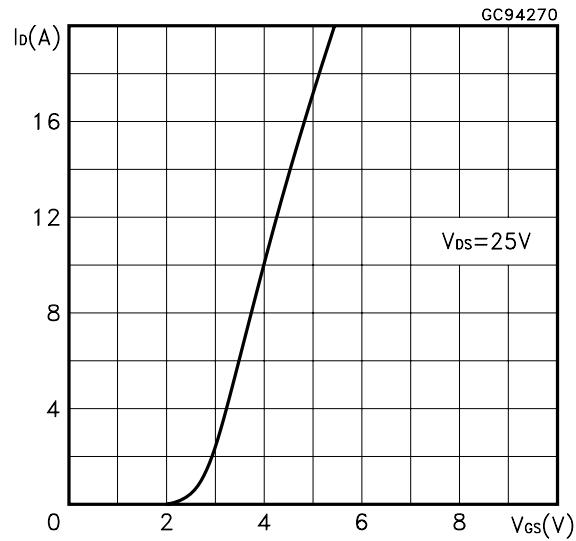
(\bullet) Pulse width limited by safe operating area.

Safe Operating Area**Thermal Impedance**

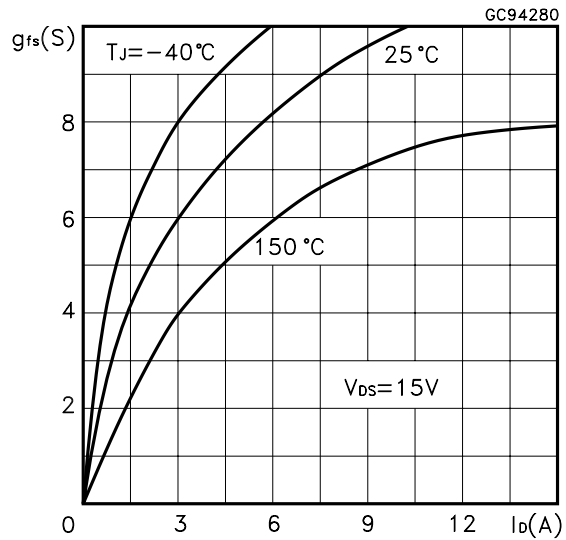
Output Characteristics



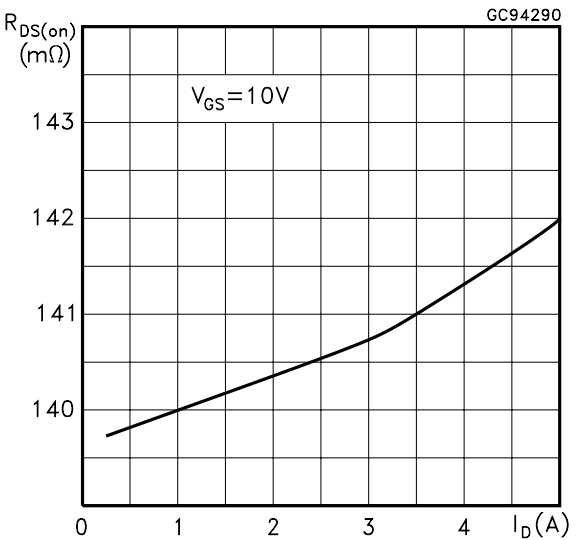
Transfer Characteristics



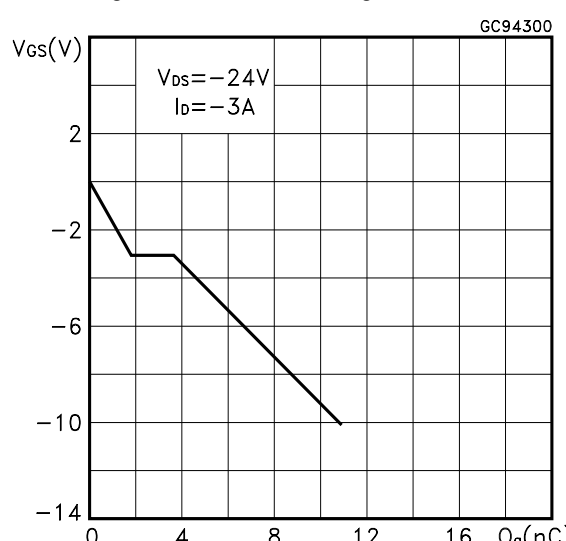
Transconductance



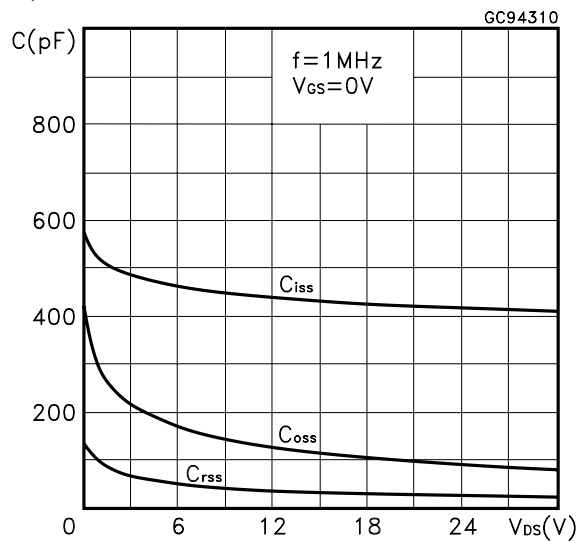
Static Drain-source On Resistance



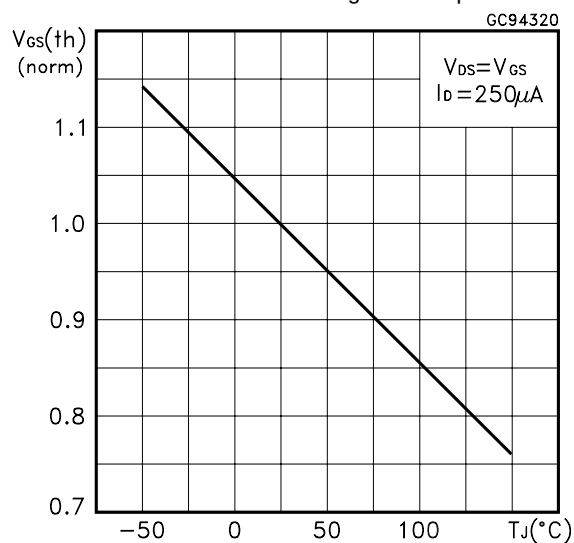
Gate Charge vs Gate-source Voltage



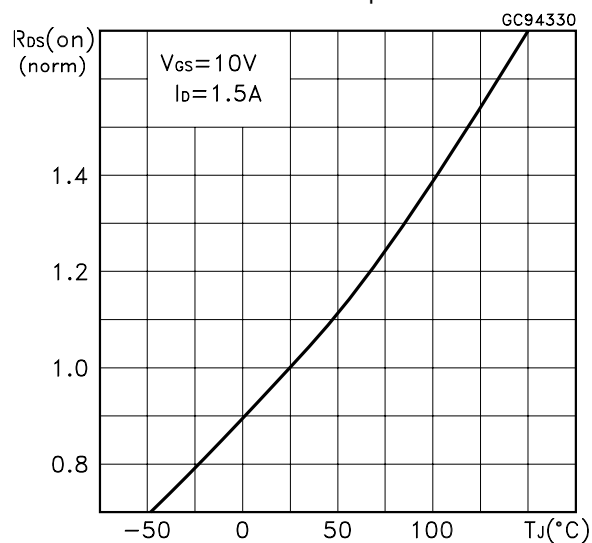
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized on Resistance vs Temperature



Source-drain Diode Forward Characteristics

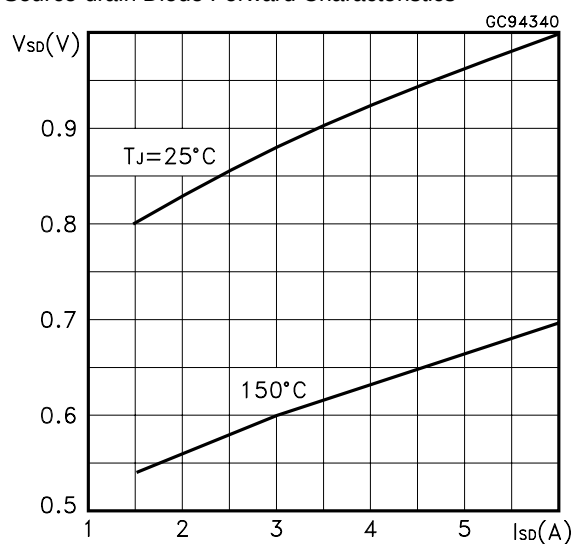


Fig. 1: Switching Times Test Circuits For Resistive Load

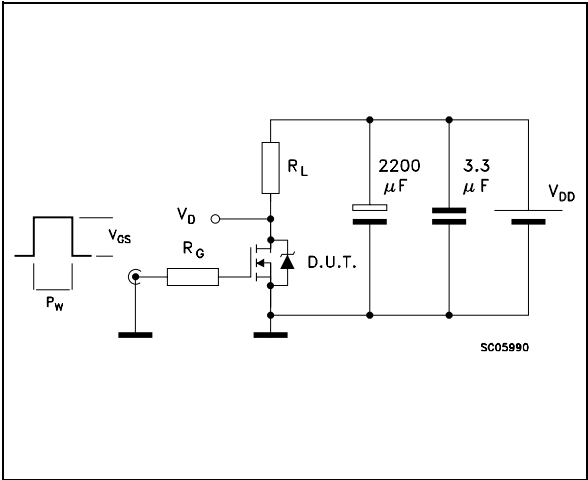


Fig. 2: Gate Charge test Circuit

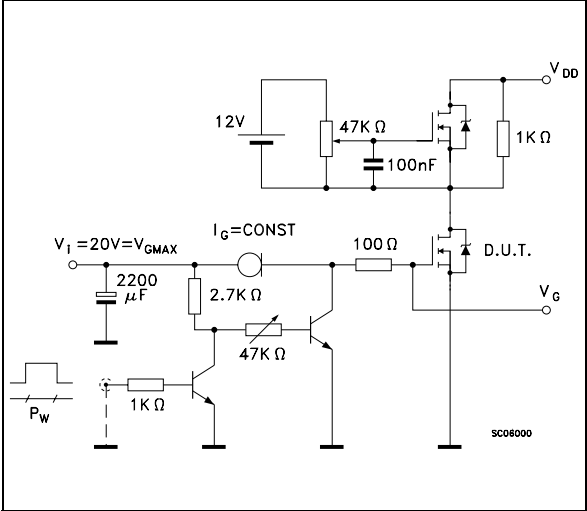
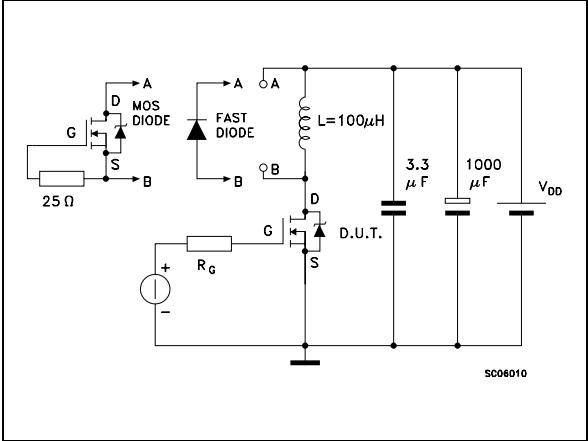
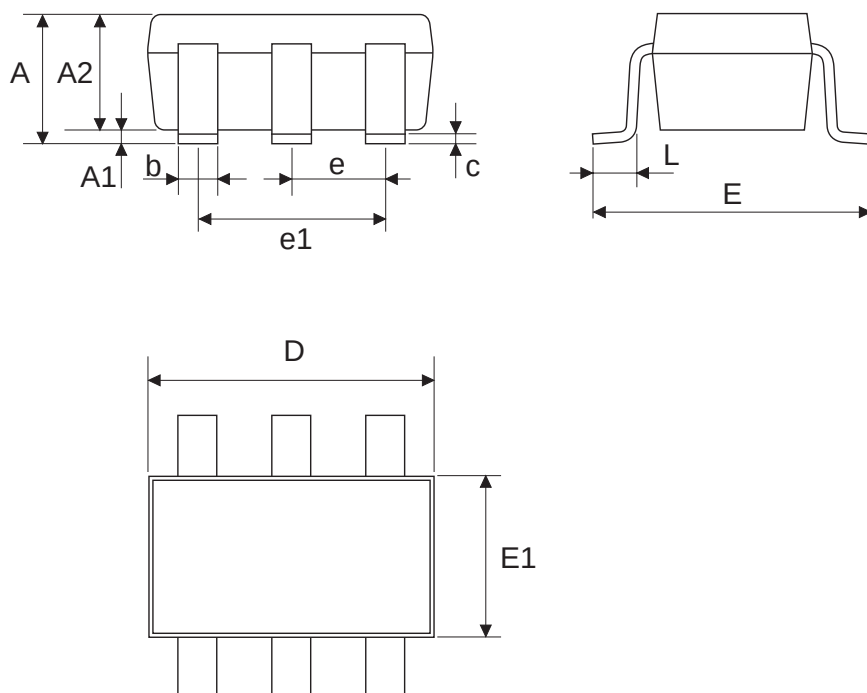


Fig. 3: Test Circuit For Diode Recovery Behaviour



SOT23-6L MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.90		1.45	0.035		0.057
A1	0.00		0.15	0.000		0.006
A2	0.90		1.30	0.035		0.051
b	0.25		0.50	0.010		0.020
C	0.09		0.20	0.004		0.008
D	2.80		3.10	0.110		0.122
E	2.60		3.00	0.102		0.118
E1	1.50		1.75	0.059		0.069
L	0.35		0.55	0.014		0.022
e		0.95			0.037	
e1		1.90			0.075	



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